

P-Channel 20-V(D-S) MOSFET

V(BR)DSS	RDS(on)MAX	ID
-20 V	92mΩ@-10V	-2A
	118mΩ@-4.5V	
	166mΩ@-2.5V	

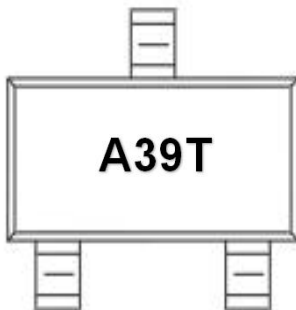
FEATURE

- ※ TrenchFET Power MOSFET
- ※ ESD Rating : 2000V HBM

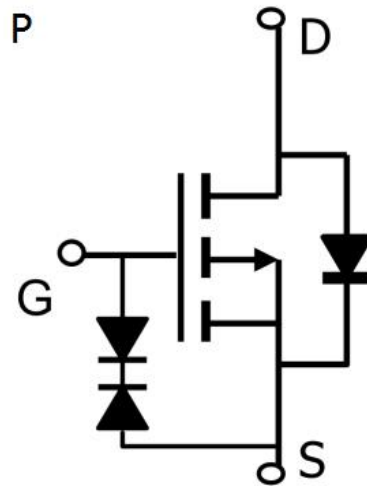
APPLICATION

- ※ Load Switch for Portable Devices
- ※ DC/DC Converter

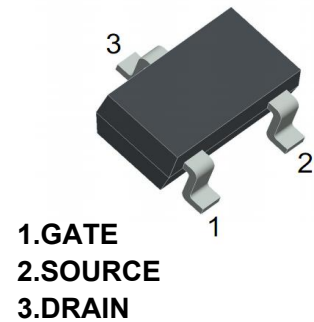
MARKING



Equivalent Circuit



SOT-23



Maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	-2	A
Pulsed Diode Current	IDM	-8	
Power Dissipation	PD	1.4	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	125	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	

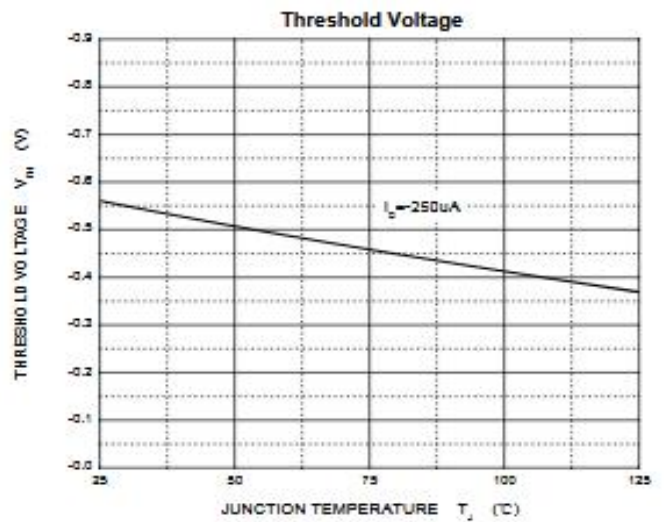
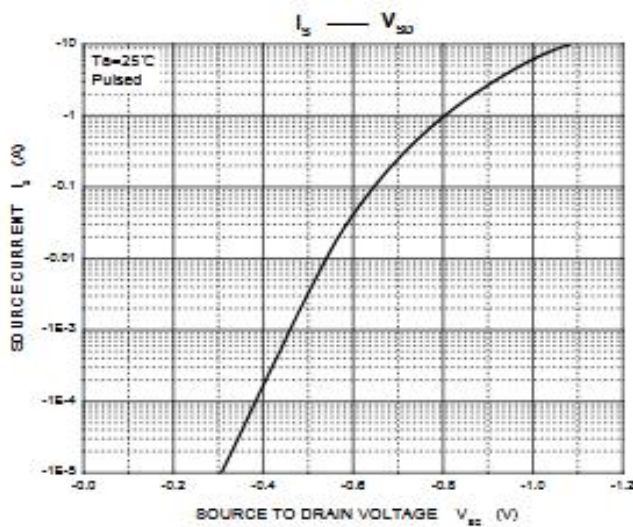
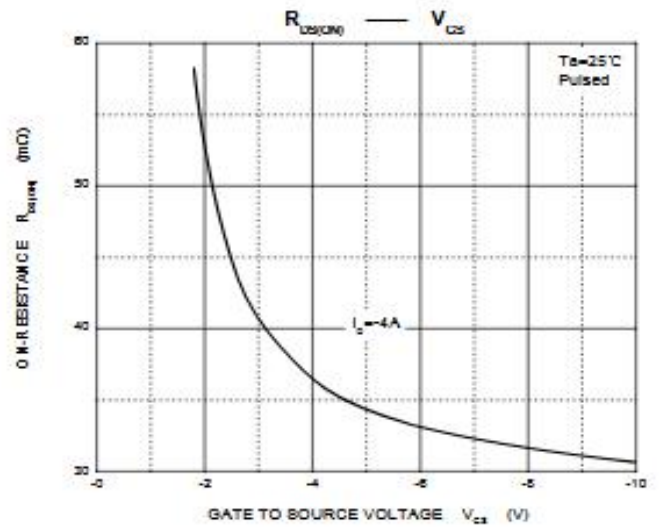
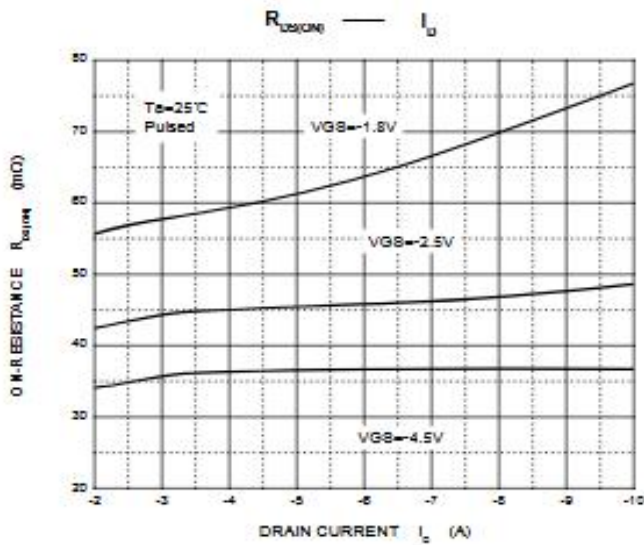
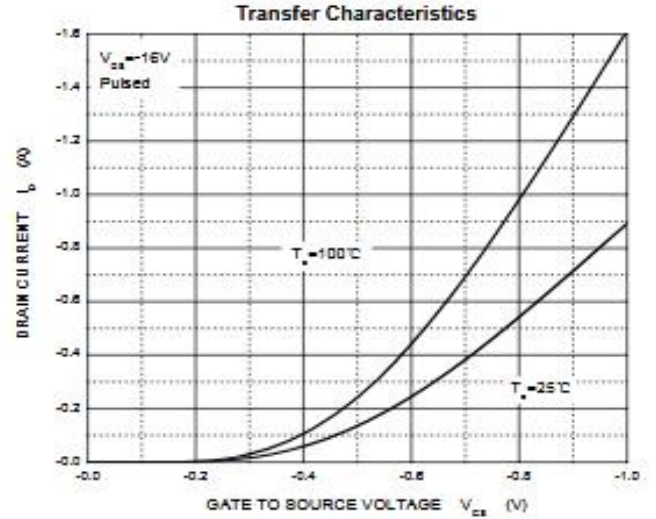
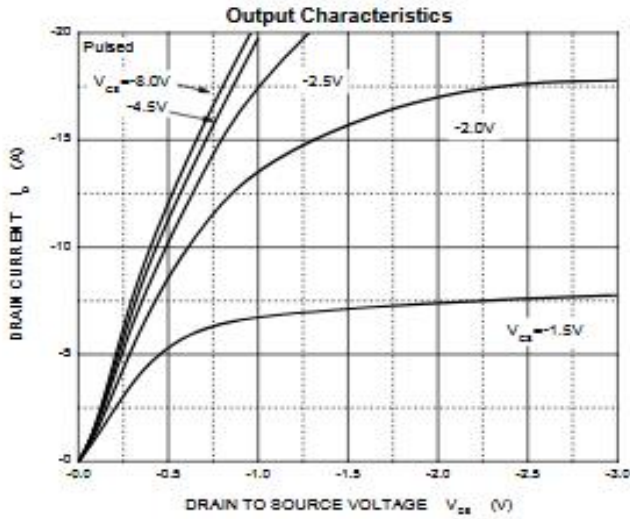
MOSFET ELECTRICAL CHARACTERISTICS
Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-20			V
Gate-source threshold voltage	VGS(th)	VDS = VGS, ID = -250μA	-0.6		-1.4	V
Gate-source leakage	IGSS	VDS = 0V, VGS = ±12V			±10	μA
Zero gate voltage drain current	IDSS	VDS = -16V, VGS = 0V			-1	μA
Drain-source on-state resistancea	RDS(on)	VGS = -10V, ID = -2A			92	mΩ
		VGS = -4.5V, ID = -2A			118	mΩ
		VGS = -2.5V, ID = -1A			166	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -2A		6.8		S
Diode forward voltage	VSD	IS=1A, VGS=0V		-0.8	-1.3	V
Dynamic						
Input capacitance	Ciss	VDS = -10V, VGS = 0V, f=1MHz		512		pF
Output capacitance	Coss			77		pF
Reverse transfer capacitanceb	Crss			62		pF
Total gate charge	Qg	VDS = -10V, VGS = -4.5V, ID = -2A		2.5		nC
Gate-source charge	Qgs			0.8		nC
Gate-drain charge	Qgd			2		nC
Gate resistance	Rg	f=1MHz		6.5		Ω
Switchingb						
Turn-on delay time	td(on)	VDS= -10V RL=5Ω, ID ≈ -1A, VGEN=- 10V, Rg=3Ω		5		ns
Rise time	tr			6.7		ns
Turn-off delay time	td(off)			28		ns
Fall time	tf			13.5		ns
Body Diode Reverse Recovery Time	Trr	IF= -2A, dI/dt=100A/μs		9.8	12	ns
Body Diode Reverse Recovery Charge	Qrr	IF= -2A, dI/dt=100A/μs		2.7		nC

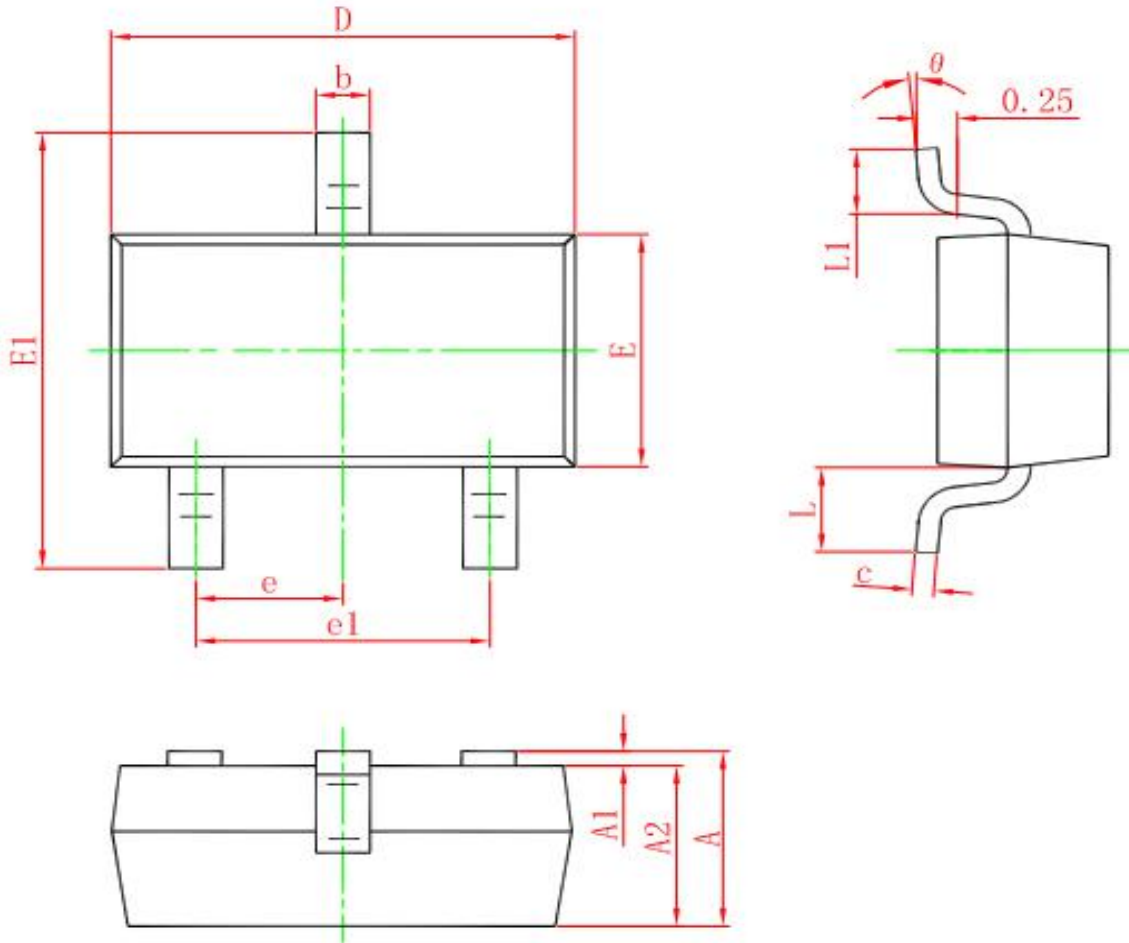
Note :

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

Typical Characteristics:



SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°